

Key Features

Frequency:	0.7-6GHz	Drain Efficiency:	40%
Typical Gain:	9dB	Offset:	28V
Typical Output:	44dBm (CW)	Package Mode:	Cermet

Introduction

ERI0760-P44-CW is 0.7-6.0GHz high power and efficiency GaN IMFET power transistor. It works with dual power supply, $V_{ds}=28V$, and can provide 44dBm output power in 0.7-6.0GHz, power gain is 9dB, drain efficiency is 40%.

Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Mark
Vd	Drain Voltage	40V	
Vg	Gate Voltage	-5V	
Pd	Power Dissipation	100W	25°C
Tch	Channel Temperature	225°C	[1]
Tm	Mount Temperature	300°C	1min, N ₂ Protection
Tstg	Storage Temperature	-55 ~ 175°C	

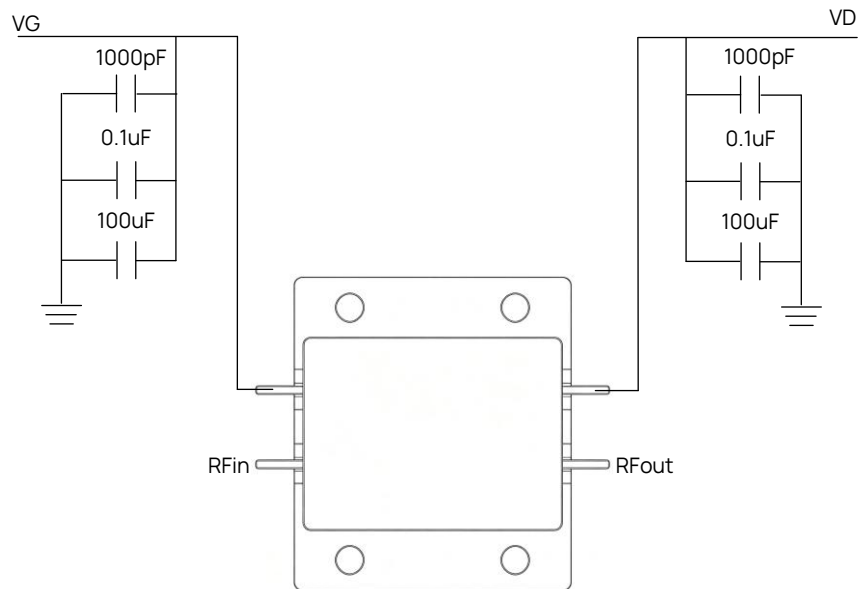
[1] Higher than any values above may cause permanent damage.

Specifications (TA=25°C)

Symbol	Parameter	Values			Unit
		Min	Typ	Max	
Pout	Output Power	44	45		dBm
Gp	Power Gain	9	10		dB
nD	Drain Efficiency	40	45		%
Gp	Gain Flatness	-1		+1	dB
Rth	Thermal resistance		2		°C/W

Test condition: $V_{d}=28V$, $I_{d}=0.5A$, $P_{in}=35dBm$

Recommended Circuit

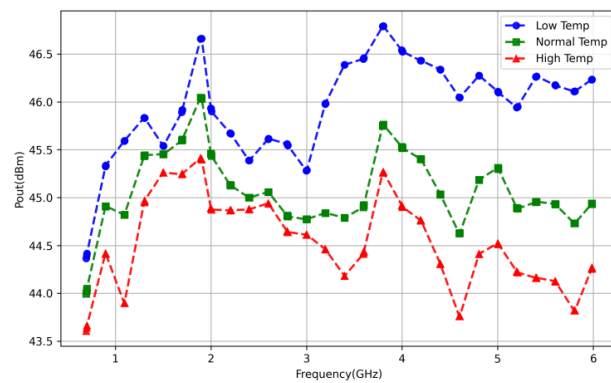


Note:

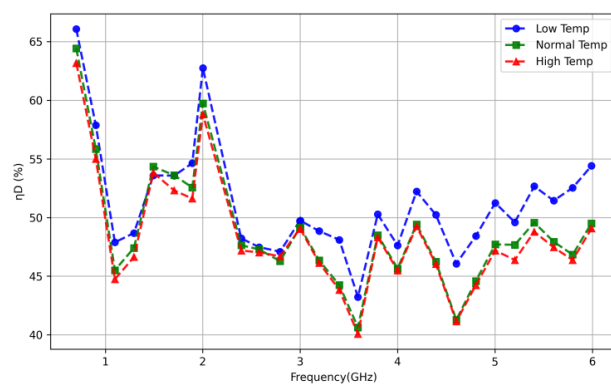
1. Power on sequence: $V_g \rightarrow V_d$. Power off Sequence: $V_d \rightarrow V_g$
2. It's high power component, attention the thermal dissipation, Working Temp should $\leq 85^\circ\text{C}$
3. Due to high Input VSWR, isolation measures need to be adopted at the input end.

Typical Performances

Pout



Drain Efficiency



Dimension (Unit: mm)

